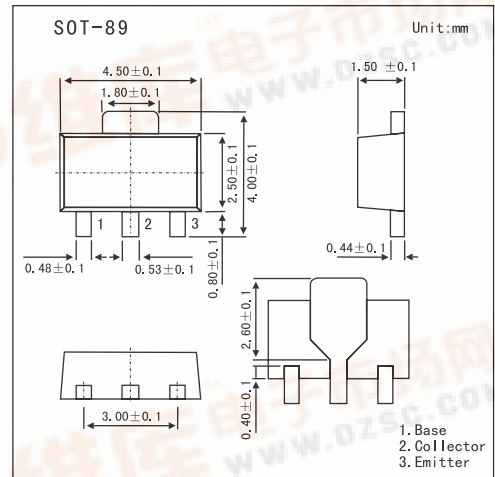


SMD Type Transistors

Silicon PNP Epitaxial
2SB1026



Features

- Low frequency power amplifier

Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-120	V
Collector to emitter voltage	V _{CEO}	-100	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-1	A
Collector peak current	i _{C(peak)} *1	-2	A
Collector power dissipation	P _C *2	1	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to 150	°C

*1 PW ≤ 10 ms, Duty cycle ≤ 20%

*2 Value on the alumina ceramic board (12.5X 20X 0.7 mm)

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10 μA, I _E = 0	-120			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1 mA, R _{BE} = ∞	-100			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10 μA, I _C = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -100 V, I _E = 0			-10	μA
DC current transfer ratio	h _{FE}	V _{CE} = -5 V, I _C = -150mA,	60		200	
		V _{CE} = -5 V, I _C = -500mA	30			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -0.5 A, I _B = -50 mA,			-1.0	V
Base to emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -150mA,			-0.9	V
Gain bandwidth product	f _T	V _{CE} = -5 V, I _C = -150 mA		140		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz		20		pF

hFE Classification

Marking	DL	DM
hFE	60 to 120	100 to 200

